

Southern Illinois University at Carbondale

Syllabus

ECE 557 Computational Electronics I

Catalog Description: Computers and computing. High-performance clusters or supercomputers and essential software tools. Essential numerical methods. Fundamentals of charge transport in semiconductor devices. Modeling electrostatics. Solving continuity equations. Electronic bandstructure calculations. Modeling scattering processes and carrier mobility. Phonon transport and thermoelectrics. Fundamentals of optical processes. Commercial and non-commercial semiconductor device modeling tools.

Course Total Credit Hours: 3

Lecture: 3

Prerequisites: ECE 447 or Instructor consent.

Objectives:

- Give a general introduction to *high-performance* large-scale scientific computing.
- Understand how advanced scientific modeling and simulation can pave the way for semiconductor device optimization and discovery.
- Understand the essential *physical processes* governing the operation of current state-of-the-art semiconductor devices.
- Develop software for modeling classical and semi-classical transport processes
- Students will be using both commercial and available non-commercial software tools to validate their models and study various aspects of semiconductor devices.
- Write reports/articles as per IEEE Author Guidelines and publish on www.

Laboratory Fees: None

Laboratory safety equipment: None

Instructor: Dr. Shaikh S. Ahmed, Associate Professor, ECE Department, SIUC.

Course Committee: *Department of Electrical and Computer Engineering Faculty.*

Text Book: *The subject matter for this course will be heavily drawn from the research literature and extensive references will be provided in the class notes. A useful book:*

Dragica Vasileska, Stephen M. Goodnick, and Gerhard Klimeck, *Computational Electronics: Semiclassical and Quantum Device Modeling and Simulation*, 1st Edition, CRC Press, June 2, 2010.

References:

- Mark Lundstorm, Jing Guo, *Nanoscale Transistors: Device Physics, Modeling and Simulation*, Springer Verlag, December, 2005.
- Mark Lundstorm, *Fundamentals of Carrier Transport*, Cambridge University Press; 2nd edition, July 2, 2009.

Topical Outline:

Introduction:

1 lectures 2.2%

Different classes of semiconductor devices
What is meant by TMS (theory-modeling-simulation)?
Why modeling and simulation?
Multiscale modeling: Why modular approach?
Device modeling: Industry and Academia

Computers and computing:

5 lectures 11%

Computer hardware, Linux clusters, Top supercomputer centers in the world
Computer software:
(a) Operating system: Linux operating system, shell commands and shell scripting, X11, accessing Linux machine from Windows, cygwin
(b) Editing text with the vi editor
(c) Development tools: C/C++, FORTRAN; Makefile, debug, XML, parallel programming, CVS/subversion, valgrind, doxygen, scripting with Tcl/Python
(d) Publishing tools: data visualization, Illustrator (image creation and editing), LaTeX, IEEE and APS author guides
(e) Software deployment using Rappture

Essential numerical methods:

4 lectures 8.8%

Finding roots, integration, differentiation
Solving differential equations:
Discretization into a matrix equation, solving matrices, eigenvalues and eigenvectors
Polynomial fitting
Monte Carlo method

Fundamentals of carrier transport:

3 lectures 6.6%

Drude's model
Landauer's model and ballistic transport
Wave equations
Quantum transport equations
Boltzmann Transport Equation
Drift-Diffusion model
Hydrodynamic model
Ballistic model

Modeling electrostatics

4 lectures 8.8%

Poisson's equation
Analytical solution
Numerical solution: Discretization, Boundary conditions, Matrix inversion

Solving continuity equations:

3 lectures 6.6%

Numerical solutions of the electron-hole continuity equations

Electronic bandstructure calculation:	5 lectures	11%
Numerical solution of Schrödinger equation		
Wave packet dynamics		
Periodic potential and the Kronig-Penny model		
Bandstructure calculation using the tight-binding method:		
Theory, implementation, case study on a graphene lattice		
Electron density of states and effective mass		
Modeling scattering processes and carrier mobility:	5 lectures	11%
Phonon modes		
Perturbation theory		
Scattering rate calculation		
RTA and Rhode's iterative method for mobility modeling		
Various mobility models		
Phonon transport and thermoelectrics:	3 lectures	6.6%
Thermal conductivity		
Self-heating in semiconductor devices		
ZT figure-of-merit of thermoelectric devices		
Fundamentals of optical processes:	3 lectures	6.6%
Optical transition rate		
Internal and external quantum efficiency		
Efficiency <i>droop</i> and lumen depreciation		
Commercial and non-commercial semiconductor device modeling tools:	4 lectures	8.8%

Grading:

Homework	50%
Project	25%
Final Exam	25%

Letter grade: **A:** 90-100 **B:** 80-89 **C:** 70-79 **D:** 60-69 **F:** <60